Low-power 3-input EXCLUSIVE-OR gate Rev. 4 — 5 August 2010

Product data sheet

General description 1.

The 74AUP1G386 provides a single 3-input EXCLUSIVE-OR gate.

Schmitt trigger action at all inputs makes the circuit tolerant to slower input rise and fall times across the entire V_{CC} range from 0.8 V to 3.6 V.

This device ensures a very low static and dynamic power consumption across the entire V_{CC} range from 0.8 V to 3.6 V.

This device is fully specified for partial power-down applications using IOFF. The I_{OFF} circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

Features and benefits 2.

- Wide supply voltage range from 0.8 V to 3.6 V
- High noise immunity
- Complies with JEDEC standards:
 - JESD8-12 (0.8 V to 1.3 V)
 - JESD8-11 (0.9 V to 1.65 V)
 - JESD8-7 (1.2 V to 1.95 V)
 - JESD8-5 (1.8 V to 2.7 V)
 - JESD8-B (2.7 V to 3.6 V)
- ESD protection:
 - HBM JESD22-A114F Class 3A exceeds 5000 V
 - MM JESD22-A115-A exceeds 200 V
 - CDM JESD22-C101E exceeds 1000 V
- Low static power consumption; I_{CC} = 0.9 μA (maximum)
- Latch-up performance exceeds 100 mA per JESD 78 Class II
- Inputs accept voltages up to 3.6 V
- Low noise overshoot and undershoot < 10 % of V_{CC}
- I_{OFF} circuitry provides partial Power-down mode operation
- Multiple package options
- Specified from –40 °C to +85 °C and –40 °C to +125 °C



Low-power 3-input EXCLUSIVE-OR gate

3. Ordering information

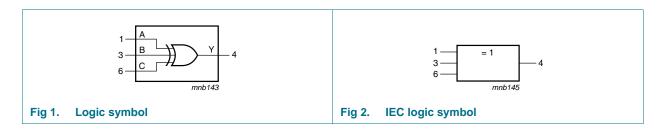
Table 1. Orderin	able 1. Ordering information						
Type number	Package						
	Temperature range	Name	Description	Version			
74AUP1G386GW	–40 °C to +125 °C	SC-88	plastic surface-mounted package; 6 leads	SOT363			
74AUP1G386GM	–40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 \times 1.45 \times 0.5 mm	SOT886			
74AUP1G386GF	–40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 \times 1 \times 0.5 mm	SOT891			
74AUP1G386GN	–40 °C to +125 °C	XSON6	extremely thin small outline package; no leads; 6 terminals; body $0.9 \times 1.0 \times 0.35$ mm	SOT1115			
74AUP1G386GS	–40 °C to +125 °C	XSON6	extremely thin small outline package; no leads; 6 terminals; body $1.0 \times 1.0 \times 0.35$ mm	SOT1202			

4. Marking

Table 2. Marking	
Type number	Marking code ^[1]
74AUP1G386GW	aH
74AUP1G386GM	aH
74AUP1G386GF	aH
74AUP1G386GN	aH
74AUP1G386GS	аН

[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

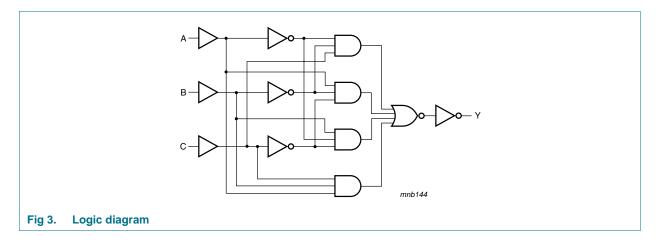
5. Functional diagram



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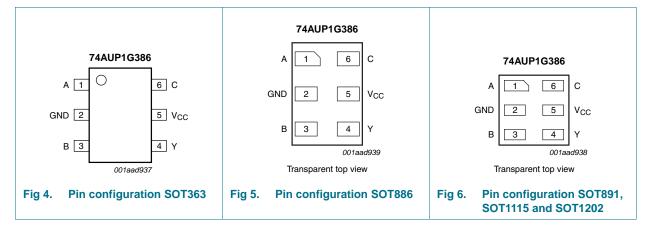
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6. Pinning information

6.1 Pinning



6.2 Pin description

Table 3.	Pin description	
Symbol	Pin	Description
A	1	data input A
GND	2	ground (0 V)
В	3	data input B
Y	4	data output Y
V _{CC}	5	supply voltage
С	6	data input C

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7. Functional description

Table 4.	Function table ^[1]		
Input			Output
Α	В	C	Y
L	L	L	L
L	L	Н	н
L	н	L	н
L	Н	Н	L
Н	L	L	н
Н	L	Н	L
Н	Н	L	L
Н	Н	Н	Н

[1] H = HIGH voltage level; L = LOW voltage level; X = don't care.

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-0.5	+4.6	V
I _{IK}	input clamping current	V _I < 0 V	-50	-	mA
VI	input voltage		<u>[1]</u> –0.5	+4.6	V
I _{OK}	output clamping current	V _O < 0 V	-50	-	mA
Vo	output voltage	Active mode and Power-down mode	<u>[1]</u> –0.5	+4.6	V
lo	output current	$V_{O} = 0 V$ to V_{CC}	-	±20	mA
I _{CC}	supply current		-	50	mA
I _{GND}	ground current		-50	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	$T_{amb} = -40 \ ^{\circ}C \ to \ +125 \ ^{\circ}C$	[2] _	250	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For SC-88 packages: above 87.5 $^\circ\text{C}$ the value of P_{tot} derates linearly with 4.0 mW/K.

For XSON6 packages: above 118 °C the value of Ptot derates linearly with 7.8 mW/K.

9. Recommended operating conditions

Table 6.	Recommended	operating	conditions
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Symbol	Parameter	Conditions	Min	Мах	Unit
V _{CC}	supply voltage		0.8	3.6	V
VI	input voltage		0	3.6	V

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Table 6.	Recommended operating conditi	onscontinued			
Symbol	Parameter	Conditions	Min	Max	Unit
Vo	output voltage	Active mode	0	V_{CC}	V
		Power-down mode; $V_{CC} = 0 V$	0	3.6	V
T _{amb}	ambient temperature		-40	+125	°C
$\Delta t / \Delta V$	input transition rise and fall rate	$V_{CC} = 0.8 V \text{ to } 3.6 V$	0	200	ns/V

Table 6. Recommended operating conditions ...continued

10. Static characteristics

Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Uni
T _{amb} = 2	5 °C					
V _{IH}	HIGH-level input voltage	$V_{CC} = 0.8 V$	$0.70 \times V_{CC}$	-	-	V
		$V_{CC} = 0.9 V$ to 1.95 V	$0.65 \times V_{CC}$	-	-	V
		V_{CC} = 2.3 V to 2.7 V	1.6	-	-	V
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	2.0	-	- - 0.30 × V _{CC} 0.35 × V _{CC} 0.7 0.9 - - - - - - - - - - - - -	V
/ _{IL}	LOW-level input voltage	$V_{CC} = 0.8 V$	-	-	$0.30\times V_{CC}$	V
		$V_{CC} = 0.9 \text{ V} \text{ to } 1.95 \text{ V}$	-	-	$0.35 \times V_{CC}$	V
		V_{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	-	-	0.9	V
/ _{ОН}	HIGH-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		I_O = –20 $\mu\text{A};V_{CC}$ = 0.8 V to 3.6 V	$V_{CC}-0.1$	-	-	V
		$I_0 = -1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	$0.75\times V_{CC}$	-	-	V
		$I_{O} = -1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	1.11	-	-	V
		$I_{O} = -1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	1.32	-	-	V
		$I_0 = -2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	2.05	-	-	V
		$I_{O} = -3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.9	-	-	V
		$I_0 = -2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.72	-	-	V
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.6	-	-	V
/ _{OL}	LOW-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		I_{O} = 20 $\mu A; V_{CC}$ = 0.8 V to 3.6 V	-	-	0.1	V
		$I_0 = 1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	-	-	$0.3\times V_{CC}$	V
		$I_0 = 1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	-	-	0.31	V
		$I_0 = 1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	-	-	0.31	V
		$I_0 = 2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.31	V
		$I_0 = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.44	V
		$I_0 = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.31	V
		$I_0 = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.44	V
	input leakage current	$V_{\rm I}$ = GND to 3.6 V; $V_{\rm CC}$ = 0 V to 3.6 V	-	-	±0.1	μA
OFF	power-off leakage current	V_{I} or V_{O} = 0 V to 3.6 V; V_{CC} = 0 V	-	-	±0.2	μA
IOFF	additional power-off leakage current	$V_1 \text{ or } V_0 = 0 \text{ V to } 3.6 \text{ V;}$ $V_{CC} = 0 \text{ V to } 0.2 \text{ V}$	-	-	±0.2	μA

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
сс	supply current	$\label{eq:VI} \begin{array}{l} V_{I} = GND \text{ or } V_{CC}; \ I_{O} = 0 \ A; \\ V_{CC} = 0.8 \ V \ \text{to} \ 3.6 \ V \end{array}$	-	-	0.5	μA
∆l _{CC}	additional supply current	$\label{eq:VI} \begin{array}{l} V_{I} = V_{CC} - 0.6 \; V; \; I_{O} = 0 \; A; \\ V_{CC} = 3.3 \; V \end{array}$	-	-	40	μA
Cı	input capacitance	V_{CC} = 0 V to 3.6 V; V_{I} = GND or V_{CC}	-	0.8	-	pF
Co	output capacitance	$V_O = GND; V_{CC} = 0 V$	-	1.7	-	pF
r _{amb} = −4	40 °C to +85 °C					
/ _{IH}	HIGH-level input voltage	$V_{CC} = 0.8 V$	$0.70\times V_{CC}$	-	-	V
		$V_{CC} = 0.9 \text{ V} \text{ to } 1.95 \text{ V}$	$0.65 \times V_{CC}$	-	-	V
		V_{CC} = 2.3 V to 2.7 V	1.6	-	-	V
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	2.0	-	-	V
/ _{IL}	LOW-level input voltage	$V_{CC} = 0.8 V$	-	-	$0.30\times V_{CC}$	V
		$V_{CC} = 0.9 V$ to 1.95 V	-	-	$0.35\times V_{CC}$	V
		V_{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	-	-	0.9	V
/ _{ОН}	HIGH-level output voltage	$V_I = V_{IH} \text{ or } V_{IL}$				
		I_{O} = –20 $\mu\text{A};V_{CC}$ = 0.8 V to 3.6 V	$V_{CC}-0.1$	-	-	V
		$I_0 = -1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	$0.7\times V_{CC}$	-	-	V
		$I_0 = -1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	1.03	-	-	V
		$I_{O} = -1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	1.30	-	-	V
		$I_{O} = -2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.97	-	-	V
		$I_{O} = -3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.85	-	-	V
		$I_{O} = -2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.67	-	-	V
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.55	-	-	V
OL	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		I_{O} = 20 μ A; V_{CC} = 0.8 V to 3.6 V	-	-	0.1	V
		I _O = 1.1 mA; V _{CC} = 1.1 V	-	-	$0.3\times V_{CC}$	V
		I _O = 1.7 mA; V _{CC} = 1.4 V	-	-	0.37	V
		I _O = 1.9 mA; V _{CC} = 1.65 V	-	-	0.35	V
		$I_0 = 2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.33	V
		I _O = 3.1 mA; V _{CC} = 2.3 V	-	-	0.45	V
		$I_0 = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.33	V
		I _O = 4.0 mA; V _{CC} = 3.0 V	-	-	0.45	V
	input leakage current	$V_I = GND$ to 3.6 V; $V_{CC} = 0$ V to 3.6 V	-	-	±0.5	μA
OFF	power-off leakage current	V_{1} or $V_{0} = 0$ V to 3.6 V; $V_{CC} = 0$ V	-	-	±0.5	μΑ
I _{OFF}	additional power-off leakage current	$V_1 \text{ or } V_0 = 0 \text{ V to } 3.6 \text{ V;}$ $V_{CC} = 0 \text{ V to } 0.2 \text{ V}$	-	-	±0.6	μA
CC	supply current	$\label{eq:VI} \begin{array}{l} V_{I} = GND \text{ or } V_{CC}; \ I_{O} = 0 \ A; \\ V_{CC} = 0.8 \ V \ \text{to} \ 3.6 \ V \end{array}$	-	-	0.9	μA
Alcc	additional supply current		-	-	50	μΑ

Table 7. Static characteristics ...continued

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Low-power 3-input EXCLUSIVE-OR gate

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Γ _{amb} = –	40 °C to +125 °C					
/ _{IH}	HIGH-level input voltage	V _{CC} = 0.8 V	$0.75\times V_{CC}$	-	-	V
		$V_{CC} = 0.9 V$ to 1.95 V	$0.70\times V_{CC}$	-	-	V
	LOW-level input voltage	V_{CC} = 2.3 V to 2.7 V	1.6	-	-	V
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	2.0	-	-	V
/ _{IL}	LOW-level input voltage	$V_{CC} = 0.8 V$	-	-	$0.25\times V_{CC}$	V
		$V_{CC} = 0.9 V$ to 1.95 V	-	-	$0.30\times V_{CC}$	V
		V_{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	-	-	0.9	V
/ _{ОН}	HIGH-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		I_O = –20 $\mu\text{A};V_{CC}$ = 0.8 V to 3.6 V	V _{CC} – 0.11	-	-	V
		$I_{O} = -1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	$0.6\times V_{CC}$	-	-	V
		$I_{O} = -1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	0.93	-	-	V
		$I_{O} = -1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	1.17	-	-	V
		I_{O} = -2.3 mA; V_{CC} = 2.3 V	1.77	-	-	V
		$I_{O} = -3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.67	-	-	V
		$I_{O} = -2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.40	-	-	V
		$I_O = -4.0$ mA; $V_{CC} = 3.0$ V	2.30	-	-	V
/ _{OL}	LOW-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		I_O = 20 $\mu\text{A};V_{CC}$ = 0.8 V to 3.6 V	-	-	0.11	V
		$I_{O} = 1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	-	-	$0.33 \times V_{CC}$	V
		I_{O} = 1.7 mA; V_{CC} = 1.4 V	-	-	0.41	V
		I_{O} = 1.9 mA; V_{CC} = 1.65 V	-	-	0.39	V
		I_{O} = 2.3 mA; V_{CC} = 2.3 V	-	-	- N - N 0.25 × V _{CC} N 0.30 × V _{CC} N 0.7 N 0.9 N - N - N - N - N - N - N - N - N - N - N - N 0.11 N 0.33 × V _{CC} N 0.41 N 0.36 N 0.50 N ±0.75 N ±0.75 N ±0.75 N ±0.75 N ±0.75 N	V
		$I_{O} = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.50	V
		$I_0 = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.36	V
		I_{O} = 4.0 mA; V_{CC} = 3.0 V	-	-	0.50	V
I	input leakage current	V_{I} = GND to 3.6 V; V_{CC} = 0 V to 3.6 V	-	-	±0.75	μΑ
OFF	power-off leakage current	$V_{I} \text{ or } V_{O}$ = 0 V to 3.6 V; V_{CC} = 0 V	-	-	±0.75	μΑ
Al _{OFF}	additional power-off leakage current	$ V_{I} \text{ or } V_{O} = 0 \text{ V to } 3.6 \text{ V}; $	-	-	±0.75	μA
CC	supply current	$\label{eq:VI} \begin{array}{l} V_{I} = GND \text{ or } V_{CC}; \ I_{O} = 0 \ A; \\ V_{CC} = 0.8 \ V \ \text{to} \ 3.6 \ V \end{array}$	-	-	1.4	μA
Alcc	additional supply current		-	-	75	μA

Table 7. Static characteristics ... continued

Low-power 3-input EXCLUSIVE-OR gate

11. Dynamic characteristics

Table 8. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 8.

Symbol	Parameter	Conditions			25 °C		–40 °C to +125 °C			Unit
				Min	Typ[1]	Мах	Min	Max (85 °C)	Max (125 °C)	
C _L = 5 p	ρF									
t _{pd}	propagation delay	A, B and C to Y; see Figure 7	[2]							
		$V_{CC} = 0.8 V$		-	23.4	-	-	-	-	ns
		$V_{CC} = 1.1 \text{ V} \text{ to } 1.3 \text{ V}$		2.7	6.5	14.2	2.4	14.6	14.7	ns
		$V_{CC} = 1.4 \text{ V} \text{ to } 1.6 \text{ V}$		2.0	4.4	8.1	2.1	8.8	9.1	ns
		V_{CC} = 1.65 V to 1.95 V		1.8	3.5	6.1	1.6	7.0	7.3	ns
		V_{CC} = 2.3 V to 2.7 V		1.5	2.7	4.3	1.2	4.6	4.8	ns
		V_{CC} = 3.0 V to 3.6 V		1.3	2.4	3.6	1.0	4.0	4.2	ns
C _L = 10	pF									
t _{pd}	propagation delay	A, B and C to Y; see Figure 7	[2]							
		$V_{CC} = 0.8 V$		-	26.8	-	-	-	-	ns
		V_{CC} = 1.1 V to 1.3 V		3.2	7.3	15.8	2.7	16.2	16.3	ns
		$V_{CC} = 1.4 \text{ V} \text{ to } 1.6 \text{ V}$		2.3	5.0	9.0	2.5	9.8	10.2	ns
		V _{CC} = 1.65 V to 1.95 V		2.2	4.1	6.9	1.9	7.8	8.2	ns
		V_{CC} = 2.3 V to 2.7 V		1.9	3.2	5.0	1.6	5.3	5.5	ns
V		V_{CC} = 3.0 V to 3.6 V		1.7	2.9	4.3	1.4	4.7	4.9	ns
C _L = 15	pF									
pd	propagation delay	A, B and C to Y; see Figure 7	[2]							
		$V_{CC} = 0.8 V$		-	30.1	-	-	-	-	ns
		V_{CC} = 1.1 V to 1.3 V		3.5	8.1	17.3	3.0	17.7	17.8	ns
		$V_{CC} = 1.4 \text{ V} \text{ to } 1.6 \text{ V}$		2.6	5.6	9.8	2.8	10.7	11.1	ns
		V _{CC} = 1.65 V to 1.95 V		2.4	4.6	7.5	2.2	8.6	9.0	ns
		V_{CC} = 2.3 V to 2.7 V		2.2	3.7	5.5	1.9	5.9	6.2	ns
		V_{CC} = 3.0 V to 3.6 V		2.0	3.4	4.8	1.7	5.2	5.5	ns
C _L = 30	pF									
pd	propagation delay	A, B and C to Y; see Figure 7	[2]							
		$V_{CC} = 0.8 V$		-	37.9	-	-	-	-	ns
		$V_{CC} = 1.1 \text{ V} \text{ to } 1.3 \text{ V}$		4.5	10.3	21.6	3.9	22.0	22.1	ns
		$V_{CC} = 1.4 \text{ V} \text{ to } 1.6 \text{ V}$		3.5	7.1	12.1	3.5	13.2	13.8	ns
		V_{CC} = 1.65 V to 1.95 V		3.1	5.8	9.5	2.8	10.7	11.3	ns
		V_{CC} = 2.3 V to 2.7 V		2.9	4.8	6.9	2.6	7.8	8.2	ns
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$		2.7	4.5	6.1	2.3	6.6	6.9	ns

Low-power 3-input EXCLUSIVE-OR gate

Symbol	Parameter	Conditions		25 °C			–40 °C to +125 °C			Unit
				Min	Typ <mark>[1]</mark>	Max	Min	Мах (85 °С)	Max (125 °C)	
C _L = 5 p	F, 10 pF, 15 pF and	30 pF								
C _{PD}	power dissipation capacitance	$f_i = 1 \text{ MHz}; V_1 = \text{GND to } V_{\text{CC}}$	[3][4]							
		$V_{CC} = 0.8 V$		-	2.9	-	-	-	-	pF
		V_{CC} = 1.1 V to 1.3 V		-	3.0	-	-	-	-	pF
		V_{CC} = 1.4 V to 1.6 V		-	3.1	-	-	-	-	pF
		V_{CC} = 1.65 V to 1.95 V		-	3.3	-	-	-	-	pF
		V_{CC} = 2.3 V to 2.7 V		-	3.9	-	-	-	-	pF
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$		-	4.4	-	-	-	-	рF

Table 8. Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V); for test circuit see <u>Figure 8</u>.

[1] All typical values are measured at nominal V_{CC} .

- [2] t_{pd} is the same as t_{PLH} and t_{PHL} .
- [3] All specified values are the average typical values over all stated loads.
- [4] C_{PD} is used to determine the dynamic power dissipation (P_D in μ W).

 $P_{D} = C_{PD} \times V_{CC}^{2} \times f_{i} \times N + \Sigma (C_{L} \times V_{CC}^{2} \times f_{o}) \text{ where:}$

 f_i = input frequency in MHz;

 $f_o = output frequency in MHz;$

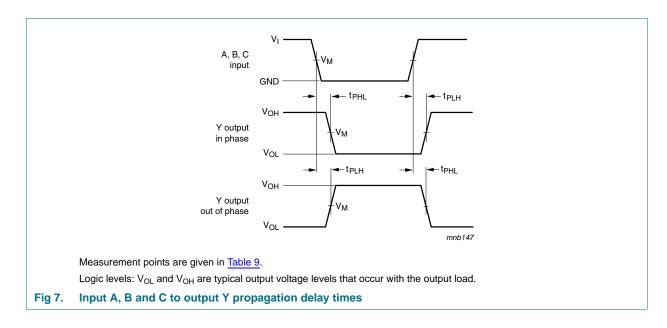
 C_L = load capacitance in pF;

 V_{CC} = supply voltage in V;

N = number of inputs switching;

 $\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of the outputs.

12. Waveforms



Low-power 3-input EXCLUSIVE-OR gate

 $t_r = t_f$

$0.5 \times V_{CC}$	$0.5\times V_{CC}$	V _{CC}	\leq 3.0 ns
	V _{CC}	V _{EXT}	
		5 κΩ	
G			
	Ť⊣LIJŤ		
		001aac521	
Test data is given in Table 10.			
Definitions for test circuit:			
R _L = Load resistance.			
C_L = Load capacitance including jig and p	robe capacitance.		
R_T = Termination resistance should be eq	ual to the output impedan	ce Z_0 of the pulse gene	rator.
V_{EXT} = External voltage for measuring sw	itching times.		
Test circuit for measuring switching	ng times		
	Test data is given in <u>Table 10</u> . Definitions for test circuit: R_L = Load resistance. C_L = Load capacitance including jig and p R_T = Termination resistance should be eq V_{EXT} = External voltage for measuring sw	Test data is given in Table 10. Definitions for test circuit: $R_L = Load$ resistance. $C_L = Load$ capacitance including jig and probe capacitance.	$V_{CC} \qquad V_{EXT} \qquad \qquad$

Input

Vм

VI

Table 9.Measurement points

Output

Vм

Supply voltage

 v_{cc}

Table 10. Test data

Supply voltage Load			V _{EXT}				
V _{CC}	CL	R _L [1]	t _{PLH} , t _{PHL}	t _{PZH} , t _{PHZ}	t _{PZL} , t _{PLZ}		
0.8 V to 3.6 V	5 pF, 10 pF, 15 pF and 30 pF	5 k Ω or 1 M Ω	open	GND	$2 \times V_{CC}$		

[1] For measuring enable and disable times $R_L = 5 k\Omega$, for measuring propagation delays, setup and hold times and pulse width $R_L = 1 M\Omega$.

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13. Package outline

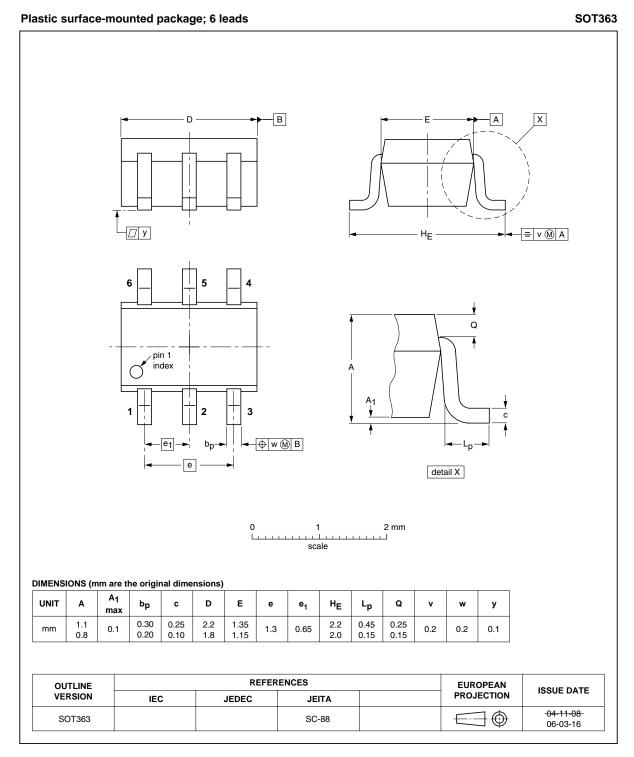


Fig 9. Package outline SOT363 (SC-88)

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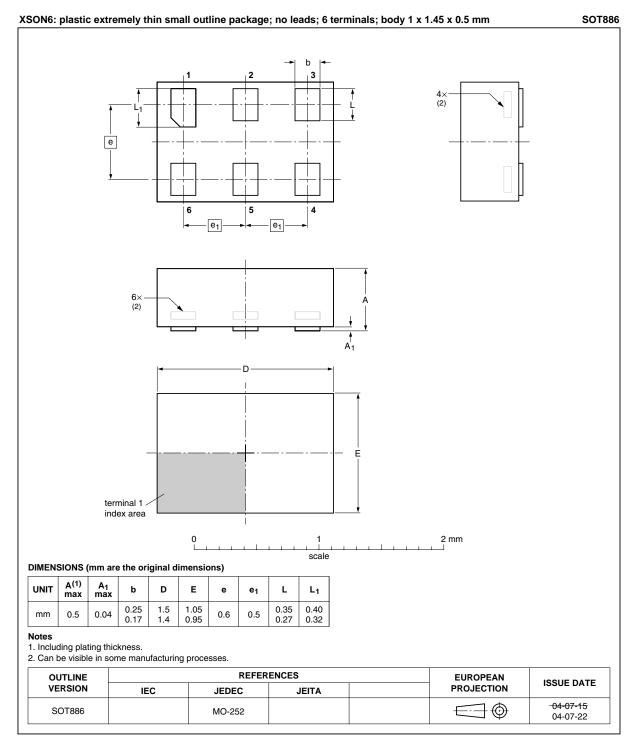


Fig 10. Package outline SOT886 (XSON6)

Product data sheet

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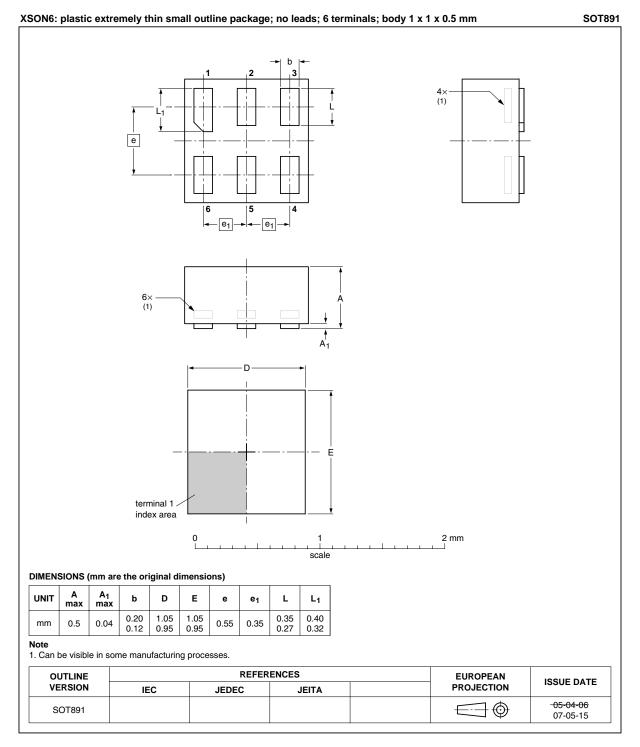
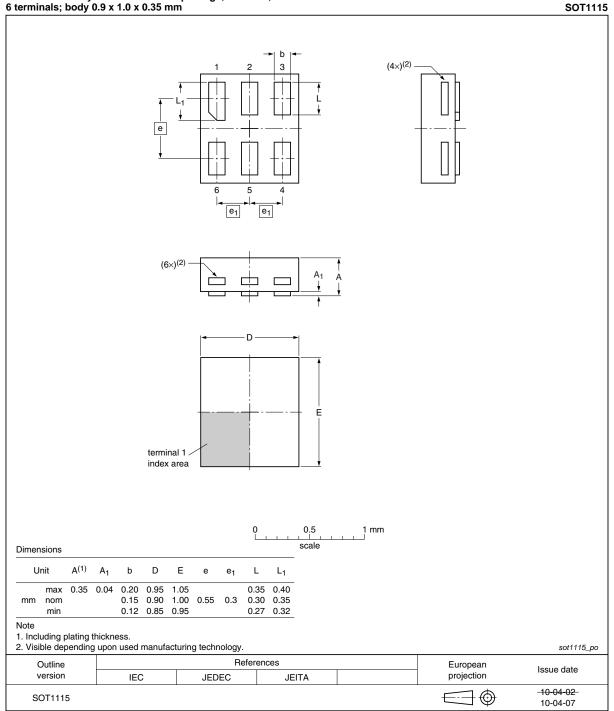


Fig 11. Package outline SOT891 (XSON6)

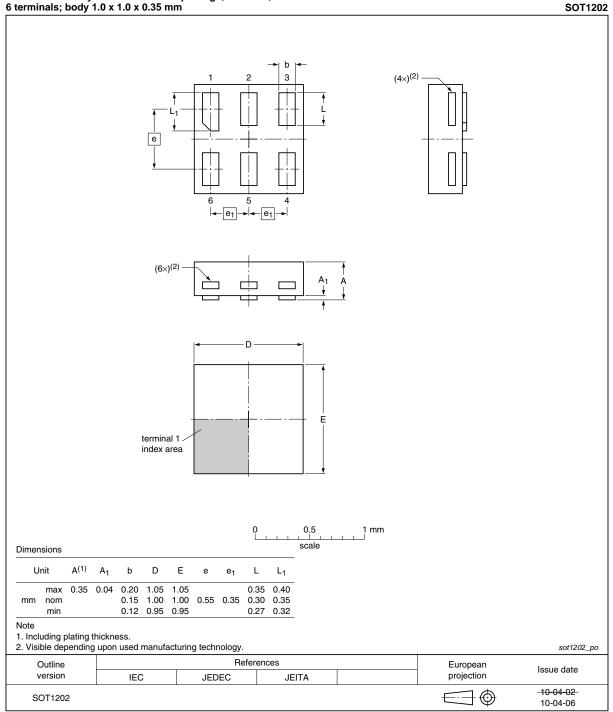
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XSON6: extremely thin small outline package; no leads; 6 terminals; body 0.9 x 1.0 x 0.35 mm

Fig 12. Package outline SOT1115 (XSON6)

Low-power 3-input EXCLUSIVE-OR gate



XSON6: extremely thin small outline package; no leads; 6 terminals; body 1.0 x 1.0 x 0.35 mm

Fig 13. Package outline SOT1202 (XSON6)

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14. Abbreviations

Table 11.	Abbreviations
Acronym	Description
CDM	Charged Device Model
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model

15. Revision history

Table 12. Revision hi	story			
Document ID	Release date	Data sheet status	Change notice	Supersedes
74AUP1G386 v.4	20100805	Product data sheet	-	74AUP1G386 v.3
Modifications:	 Added type r 	number 74AUP1G386GN (SO	T1115/XSON6 package)	
	 Added type r 	number 74AUP1G386GS (SO	T1202/XSON6 package)	
74AUP1G386 v.3	20090702	Product data sheet	-	74AUP1G386 v.2
74AUP1G386 v.2	20080110	Product data sheet	-	74AUP1G386 v.1
74AUP1G386 v.1	20061129	Product data sheet	-	-

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16. Legal information

16.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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Product data sheet

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74AUP1G386

Low-power 3-input EXCLUSIVE-OR gate

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